

C1

(c) plasma annealing ~~said~~ layer of metal nitride.

Please cancel Claim 24.

25. (Amended) The method of Claim 21, wherein said step of plasma annealing includes the steps of:

C2

exposing said metal nitride to an environment containing ions; and
electrically biasing said layer of said metal nitride to cause said ions from said environment to impact said metal nitride.

30. (Amended) The method of Claim 21, wherein said step of depositing said metal nitride and said step of plasma annealing are both performed in a single chamber and without removing a wafer on which said structure is being formed from the chamber between beginning said step of depositing said metal nitride and completion of said step of plasma annealing.

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31. (Amended) The method of Claim 21, wherein said step of depositing said metal nitride is performed using chemical vapor deposition.

32. (Amended) The method of Claim 21, wherein said step of plasma annealing includes the steps of:

performing a first plasma annealing of said metal nitride; and
performing a second plasma annealing of said metal nitride after performing said first plasma annealing.

REMARKS

Support for the above-requested amendment to Claim 21 is found at page 21, lines 13-15. Claim 24 has been cancelled. Claims 25 and 30-32 have been amended to change the dependency in view of the cancellation of Claim 24. No question of new matter arises and entry of the amendments